

REMARKS

At the outset, the Examiner is thanked for the thorough review and consideration of the subject application. The Office Action of May 16, 2005 has been received and contents carefully reviewed.

By this Amendment, Applicant amends paragraph [0033] of the specification and claims 1, 7, 11, 17 and 18. No new matter is added to the specification. Accordingly, claims 1, 3-7, 9-11 and 13-20 are currently pending in the present application. Reexamination and reconsideration of the application are respectfully requested.

In the Office Action, the amendments in paragraph [0033] of the specification made in the response field on March 4, 2005 are objected to under 35 U.S.C. § 132(a); claims 1 and 11 are objected to because of informalities; claims 1, 3-7, 9, 10, 11 and 13-20 are rejected under 35 U.S.C. § 112, first paragraph; and claims 7, 17 and 18 are rejected under 35 U.S.C. § 112, second paragraph. Applicant respectfully submits that these objections and rejections are now believed to be moot in view of the current amendments in paragraph [0033] of the specification and in claims 1, 7, 11, 17 and 18.

In addition, claims 1, 9, 11, 19 and 20 are rejected under 35 U.S.C. § 102(e) as being anticipated by Amunson et al. (U.S. Patent No. 6,545,291) in view of Nakajima et al. (U.S. Patent No. 5,710,606); and claims 1, 3-7, 9-11 and 13-20 are rejected under 35 U.S.C. § 103(a) as being unpatentable over ARA (Applicant's Related Art) in view of Amunson et al. Applicant respectfully traverses these rejections.

Claim 1 is allowable over the cited references in that claim 1 recites a combination of elements including, for example, "...a semiconductor layer on the gate insulating film and over the gate electrode; wherein the semiconductor layer includes a "E"-shaped channel having a width/length ratio of about 8.3 to about 25..." None of the cited references including Amunson et al., Nakajima et al. and ARA, singly or in combination, teaches or suggests at least this feature of the claimed invention. Accordingly, Applicant respectfully submits that claim 1 and claims 3-7 and 9-10, which depend therefrom, are allowable over the cited references.

Claim 11 is allowable over the cited references in that claim 11 recites a combination of elements including, for example, "...forming a semiconductor layer on the gate insulating film

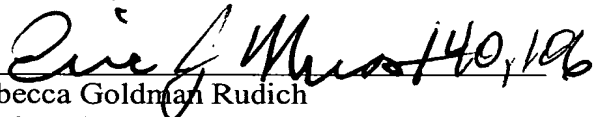
and over the gate electrode wherein the semiconductor layer forms a “E”-shaped channel having a width/length ratio of about 8.3 to about 25...” None of the cited references including Amunson et al., Nakajima et al. and ARA, singly or in combination, teaches or suggests at least this feature of the claimed invention. Accordingly, Applicant respectfully submits that claim 11 and claims 13-20, which depend therefrom, are allowable over the cited references.

Applicant believes the application is in condition for allowance and early, favorable action is respectfully solicited. If the Examiner deems that a telephone conference would further the prosecution of this application, the Examiner is invited to call the undersigned attorney at the telephone number (202) 496-7500. All correspondence should continue to be sent to the below-listed address.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911.

Dated: October 17, 2005

Respectfully submitted,

By 
Rebecca Goldman Rudich
Registration No.: 41,786
MCKENNA LONG & ALDRIDGE LLP
1900 K Street, N.W.
Washington, DC 20006
(202) 496-7500
Attorney for Applicant